

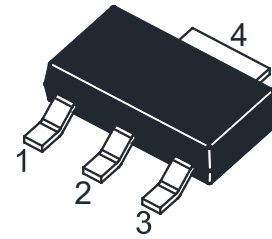
NPN Silicon Epitaxial Planar Power Transistor

Features

- Halogen and Antimony Free(HAF), RoHS compliant

Applications

- Low-side switches
- Power management
- Battery-driven devices



1.Base 2.Collector 3.Emitter 4. Collector
SOT-223 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	100	V
Collector Emitter Voltage	V_{CEO}	80	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Peak Collector Current	I_{CM}	1.5	A
Peak Base Current	I_{BM}	0.2	A
Total Power Dissipation	P_{tot}	1.33	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient ¹⁾	$R_{\theta JA}$	94	$^\circ\text{C/W}$

¹⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $V_{CE} = 2\text{ V}$, $I_C = 5\text{ mA}$	h_{FE}	25	-	-	-
at $V_{CE} = 2\text{ V}$, $I_C = 500\text{ mA}$	h_{FE}	25	-	-	-
at $V_{CE} = 2\text{ V}$, $I_C = 150\text{ mA}$	h_{FE}	63	-	160	-
	h_{FE}	100	-	250	-
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	100	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	80	-	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $I_C = 0.5\text{ A}$, $I_B = 50\text{ mA}$	$V_{CE(sat)}$	-	-	500	mV
Base Emitter Saturation Voltage at $I_C = 0.5\text{ A}$, $I_B = 50\text{ mA}$	$V_{BE(sat)}$	-	-	1.1	V
Base Emitter Voltage at $V_{CE} = 2\text{ V}$, $I_C = 0.5\text{ A}$	V_{BE}	-	-	1	V
Transition Frequency at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	130	-	MHz

Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

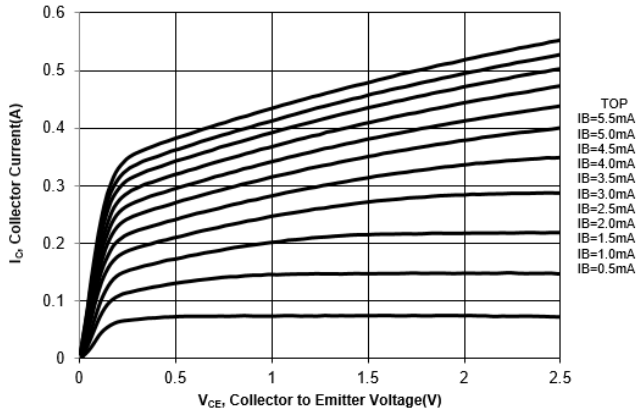


Fig. 2 Collector Current vs. Base to Emitter Voltage

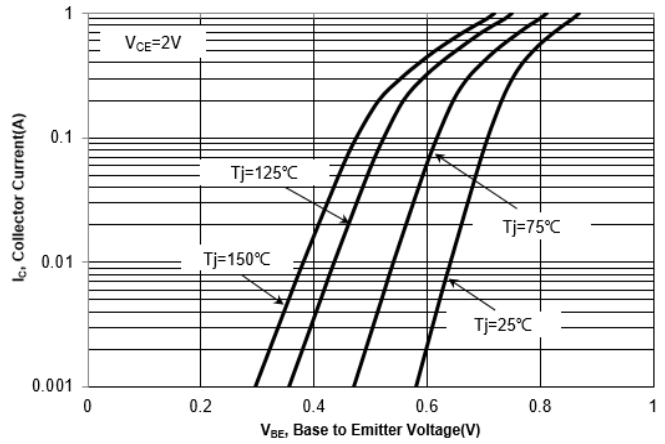


Fig. 3 $h_{FE,DC}$ Current Gain vs. Collector Current

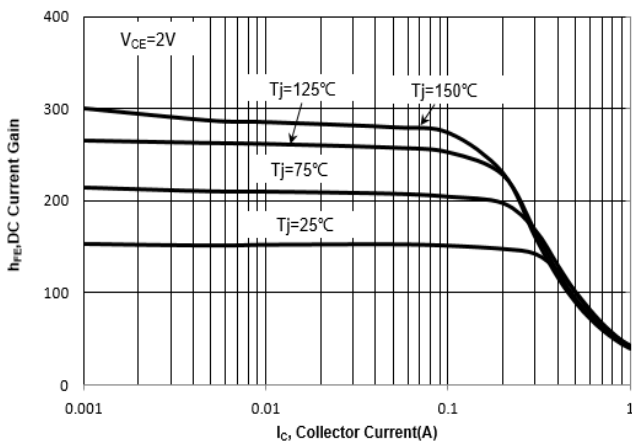
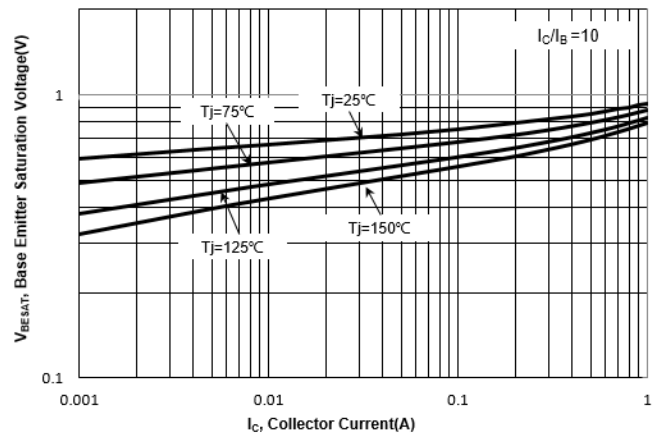


Fig. 4 $V_{BE(sat)}$ vs. Collector Current



Electrical Characteristics Curves

Fig. 5 $V_{CE(sat)}$ vs. Collector Current

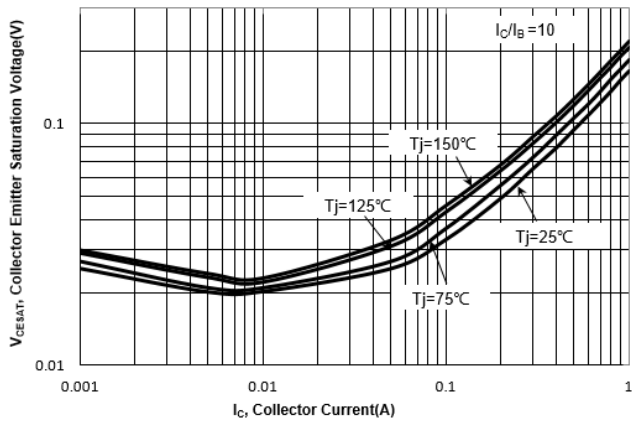


Fig. 6 Output Capacitance

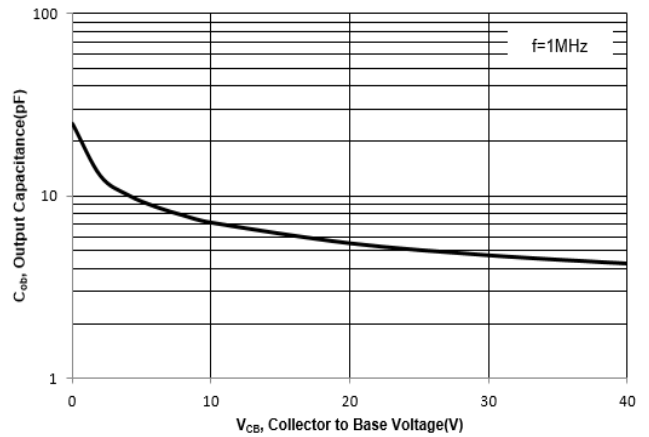
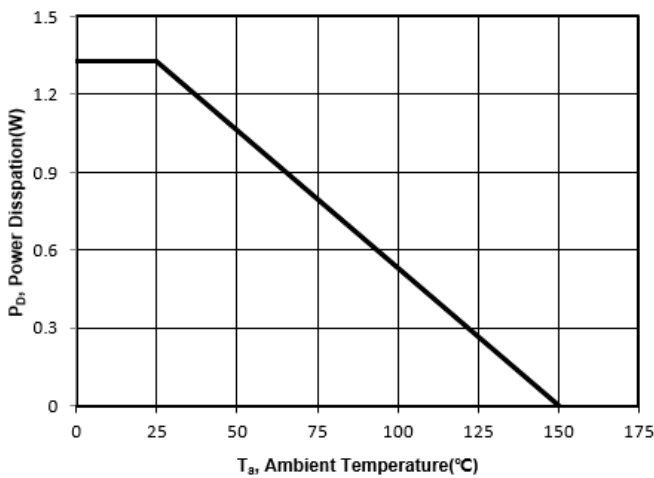


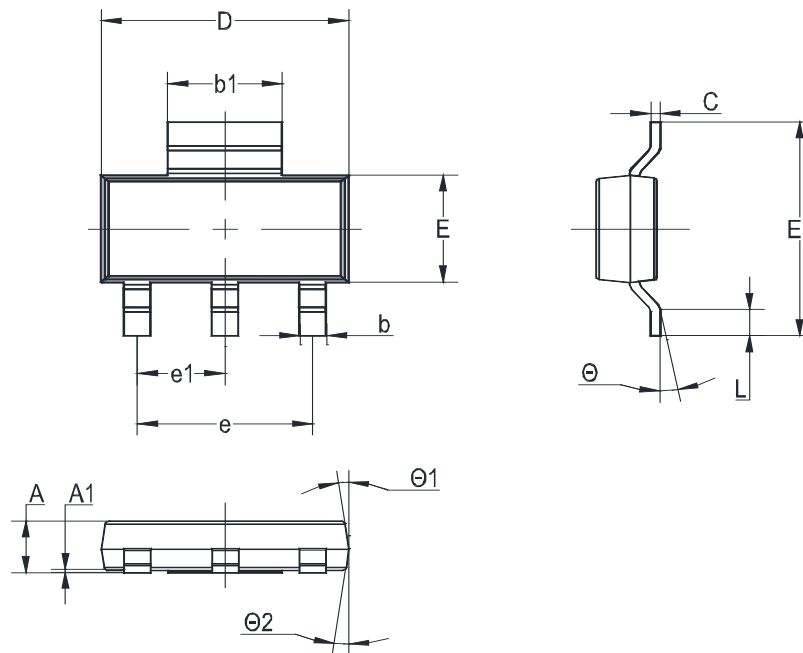
Fig 7. Power Derating Curve



BCP56-xx Series

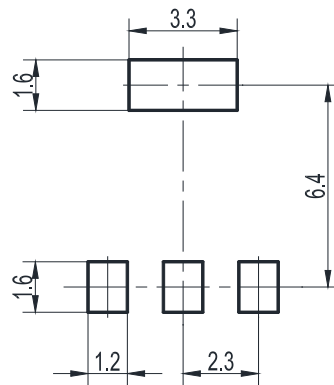
Package Outline (Dimensions in mm)

SOT-223



Unit	A	A1	b	b1	C	D	E	E1	e	e1	L	Θ	Θ1	Θ2
mm	1.8	0.1	0.8	3.1	0.32	6.7	3.7	7.3	4.6	2.3	1.1	10°	7°	7°
	1.5	MAX	0.6	2.9	0.22	6.3	3.3	6.7	TYP	TYP	0.7	0°	0°	0°

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-223	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000

Marking information

" BCP56-10Q " = Part No. (" * " = HFE grouping Code)

" **** " = Date Code Marking

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